



100V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

| BV _{DSS} | R _{DS(ON)} Max | I _D T _C = +25°C |
|-------------------|-------------------------------|--|
| 100V | 16mΩ @ V _{GS} = 10V | 44A |
| 1007 | 18mΩ @ V _{GS} = 6.0V | 41A |

Description

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize R_{DS(ON)}, yet maintain superior switching performance. This device is ideal for use in notebook battery power management and loadswitch.

Applications

- Motor Control
- DC-DC Converters
- Power Management







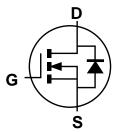
Bottom View

Features

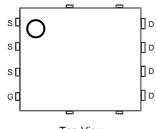
- Thermally Efficient Package Cooler Running Applications
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile Ideal for Thin Applications (PowerDI®)
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: PowerDI5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)



Internal Schematic



Top View Pin Configuration

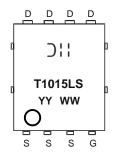
Ordering Information (Note 4)

| Part Number | Case | Packaging |
|-----------------|---------------|-------------------|
| DMT10H015LPS-13 | PowerDI5060-8 | 2,500/Tape & Reel |

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



)!! = Manufacturer's Marking T1015LS = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 17 = 2017) WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | | |
|---|-----------------|---|----------------|------------|---|
| Drain-Source Voltage | V_{DSS} | 100 | V | | |
| Gate-Source Voltage | | | V_{GSS} | ±20 | V |
| Continuous Drain Current (Note E) V 40V | Steady State | $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$ | I _D | 7.3 5.8 | А |
| Continuous Drain Current (Note 5) V _{GS} = 10V | Steady State | $T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$ | ΙD | 44 28 | А |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) | I _{DM} | 150 | Α | | |
| Maximum Continuous Body Diode Forward Current (Note | Is | 1.5 | Α | | |
| Pulsed Body Diode Forward Current (10µs Pulse, Duty Cy | I _{SM} | 150 | Α | | |
| Avalanche Current (Note 7) L = 3mH | I _{AS} | 7.5 | Α | | |
| Avalanche Energy (Note 7) L = 3mH | E _{AS} | 85 | mJ | | |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit | |
|--|----------------------------------|-------------|------|---|
| Total Power Dissipation (Note 5) | $T_A = +25^{\circ}C$ | P_{D} | 1.3 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | $R_{\theta JA}$ | 98 | °C/W | |
| Total Power Dissipation $T_C = +25^{\circ}C$ | | P_{D} | 46 | W |
| Thermal Resistance, Junction to Case | R _{0JC} | 2.7 | °C/W | |
| Operating and Storage Temperature Range | T _{J,} T _{STG} | -55 to +150 | °C | |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

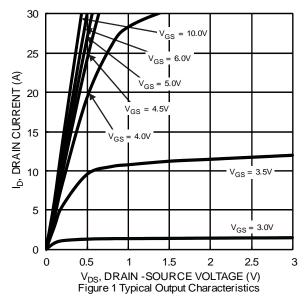
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|-----------------------------------|----------------------------------|-----|------|------|------|--|--|
| OFF CHARACTERISTICS (Note 6) | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 100 | _ | _ | V | $V_{GS} = 0V$, $I_D = 1mA$ | |
| Zero Gate Voltage Drain Current | I _{DSS} | _ | 1 | 1 | μΑ | $V_{DS} = 80V, V_{GS} = 0V$ | |
| Gate-Source Leakage | I _{GSS} | _ | _ | ±100 | nA | $V_{GS} = \pm 20V, V_{DS} = 0V$ | |
| ON CHARACTERISTICS (Note 6) | | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | 1.4 | 2.3 | 3 | V | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ | |
| | | _ | 11 | 16 | | $V_{GS} = 10V, I_D = 20A$ | |
| Static Drain-Source On-Resistance | R _{DS(ON)} | _ | 13.5 | 18 | mΩ | $V_{GS} = 6V, I_D = 20A$ | |
| | , , | _ | 18 | 25 | | V _{GS} = 4.5V, I _D = 5A | |
| Diode Forward Voltage | V_{SD} | _ | 0.9 | 1.3 | V | $V_{GS} = 0V, I_{S} = 20A$ | |
| DYNAMIC CHARACTERISTICS (Note 7) | DYNAMIC CHARACTERISTICS (Note 7) | | | | | | |
| Input Capacitance | C _{iss} | | 1871 | _ | | $V_{DS} = 50V, V_{GS} = 0V$ f = 1MHz | |
| Output Capacitance | Coss | 1 | 261 | _ | pF | | |
| Reverse Transfer Capacitance | C _{rss} | - | 6.9 | _ | | I = IIVIHZ | |
| Gate Resistance | R _G | _ | 0.75 | _ | Ω | $V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$ | |
| Total Gate Charge | Q_{G} | _ | 33.3 | _ | | V 50V L 40A | |
| Gate-Source Charge | Q _{GS} | _ | 6.9 | _ | nC | $V_{DD} = 50V, I_D = 10A,$ $V_{GS} = 10V$ | |
| Gate-Drain Charge | Q_{GD} | _ | 5.1 | _ | | VGS = 10V | |
| Turn-On Delay Time | t _{D(ON)} | _ | 6.5 | _ | | | |
| Turn-On Rise Time | t _R | _ | 7.0 | _ | | $V_{DD} = 50V, V_{GS} = 10V,$ | |
| Turn-Off Delay Time | t _{D(OFF)} | _ | 19.7 | _ | ns | $I_D = 10A$, $R_G = 6\Omega$ | |
| Turn-Off Fall Time | t _F | _ | 8.1 | _ | | | |
| Reverse Recovery Time | t _{RR} | _ | 37.9 | _ | ns | 1 100 di/dt 1000/up | |
| Reverse Recovery Charge | Q _{RR} | _ | 51.9 | _ | nC | I _F = 10A, di/dt = 100A/μs | |

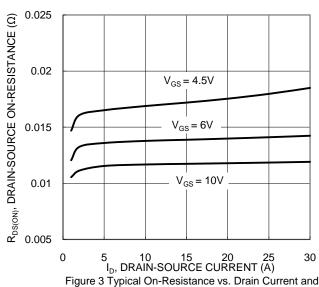
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

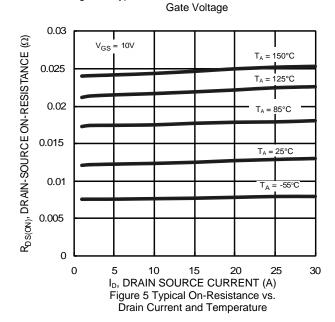
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.

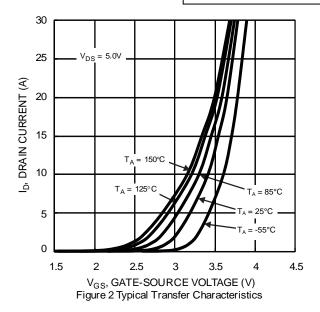


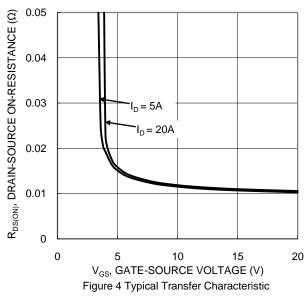


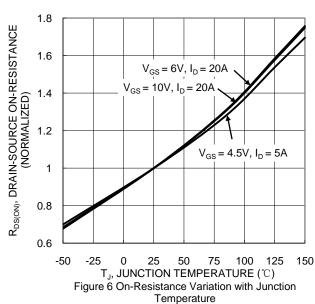






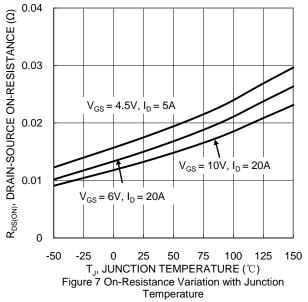


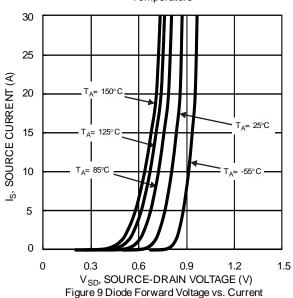


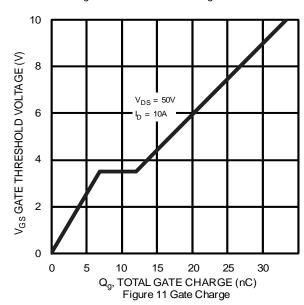












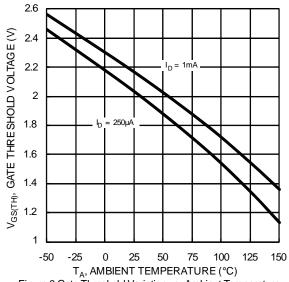
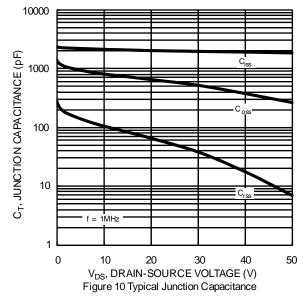
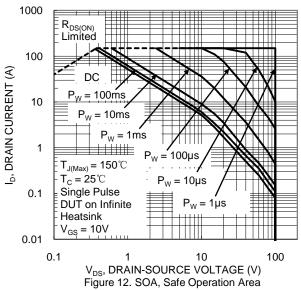
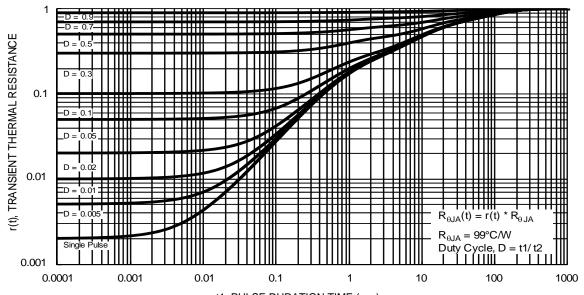


Figure 8 Gate Threshold Variation vs. Ambient Temperature









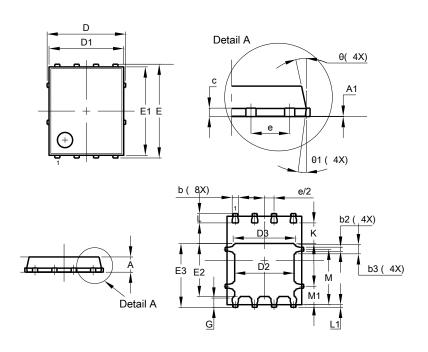
t1, PULSE DURATION TIME (sec) Figure 13 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

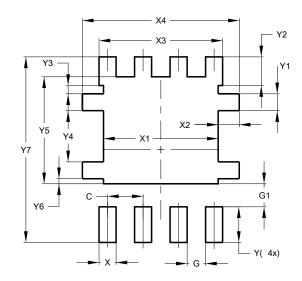


| PowerDI5060-8 | | | | | |
|----------------------|----------------|----------|-------|--|--|
| Dim | Min Max Typ | | | | |
| Α | 0.90 | 1.10 | 1.00 | | |
| A1 | 0.00 | 0.05 | - | | |
| b | 0.33 | 0.51 | 0.41 | | |
| b2 | 0.200 | 0.350 | 0.273 | | |
| b3 | 0.40 | 0.80 | 0.60 | | |
| С | 0.230 | 0.330 | 0.277 | | |
| D | | 5.15 BSC | ; | | |
| D1 | 4.70 | 5.10 | 4.90 | | |
| D2 | 3.70 | 4.10 | 3.90 | | |
| D3 | 3.90 4.30 4.10 | | | | |
| Е | 6.15 BSC | | | | |
| E1 | 5.60 | 6.00 | 5.80 | | |
| E2 | 3.28 | 3.68 | 3.48 | | |
| E3 | 3.99 | 4.39 | 4.19 | | |
| е | 1.27 BSC | | | | |
| G | 0.51 | 0.71 | 0.61 | | |
| K | 0.51 | - | - | | |
| L | 0.51 | 0.71 | 0.61 | | |
| L1 | 0.100 | 0.200 | 0.175 | | |
| М | 3.235 | 4.035 | 3.635 | | |
| M1 | 1.00 | 1.40 | 1.21 | | |
| Θ | 10° | 12° | 11° | | |
| Θ1 | 6° | 8° | 7° | | |
| All Dimensions in mm | | | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



| Dimensions | Value (in mm) | | | |
|-----------------|---------------|--|--|--|
| С | 1.270 | | | |
| G | 0.660 | | | |
| G1 | 0.820 | | | |
| Х | 0.610 | | | |
| X1 | 4.100 | | | |
| X2 | 0.755 | | | |
| Х3 | 4.420 | | | |
| X4 | 5.610 | | | |
| Υ | 1.270 | | | |
| Y1 | 0.600 | | | |
| Y2 | 1.020 | | | |
| Y3 | 0.295 | | | |
| Y4 | 1.825 | | | |
| Y5 | 3.810 | | | |
| Y6 0.180 | | | | |
| Y7 | 6.610 | | | |



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